

# Table of Contents

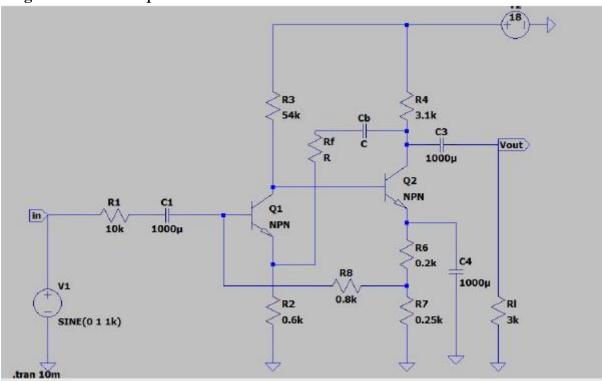
INTRODUCTION
ORIGINAL SCHEME WITH GIVEN PARAMETERS
DC ANYLISIS
EQUIVALENT DC CIRCUIT
DC COMPUTATIONS
COMPARISON OF THE SELECTED VALUES
TRANSIENT ANALYSIS
AC ANALYSIS
EQUIVALENT AC CIRCUIT
ADMITTANCE MATRIX
SMALL-SIGNAL COMPUTATIONS WITH THE NODAL ANALYSIS
EQUIVALENT AC CIRCUIT FOR THE APPROXIMATE ANALYSIS
SUITABLE TWO-PORT NETWORK ANALYSIS OF THE BETA-BLOCK
COMPUTATIONS OF SMALL-SIGNAL PARAMETERS
KUEF VERSUS FREQUENCY FROM LTSPICE
BANDWIDTH ANALYSIS
COMPUTATIONS OF ALL CAPACITORS
KUEF VERSUS FREQUENCY WITH MARKED LH AND LH POINTS
TABLE COMPARING THE VALUES OF FL AND FH

# **INRODUCTION**

An electronic circuit is a closed loop composed of individual electronic components, such as resistors, transistors, capacitors, inductors and diodes, connected by conductive wires or traces through which electric current can flow. During the 4<sup>th</sup> semester of our engineering formation we have viewed how different component of an electronic circuit work together and more importantly we have learnt how to analyzed them.

In this project report we are presenting our analysis of an electronic circuit (Project n2).

#### Original scheme and parameters



 $RL=3k\Omega$ 

 $Rg = 10 k\Omega$ 

U out max = 5V

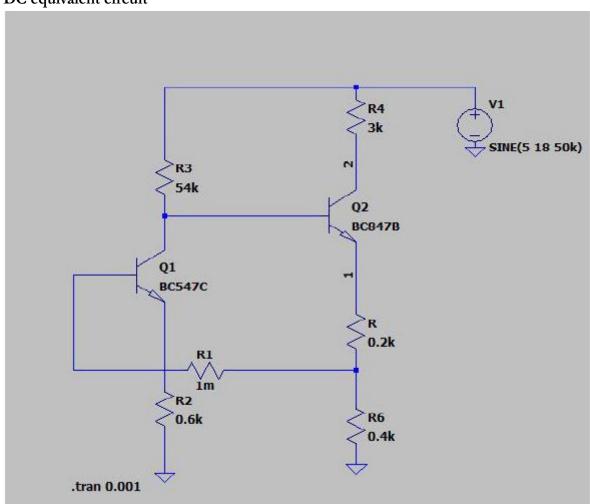
Effective gain= 40dB

Lowpass frequency=40Hz

Hi Pass= 100hz

# **DC ANALYSIS**

## DC equivalent circuit



### Assumptions:

Assumption U out max (+) = U out max (-) =U out max =5 V

 $C1=C2=CE=Cb=\infty$ 

 $U \ CEQ1(SAT) = U \ CEQ2(SAT) = 1 \ V$ 

I CQ2 = I EQ2, I CQ1 = I EQ1

U BEQ1 =0.6 V

R C2 =  $3 \text{ k}\Omega$ 

Voltage Calculations:

V CEQ = V OUT + V CESAT = 5V + 1V = 6V

V CC = V RE + V CEQ + V RC2

V CEQ = 6V

 $V RC2 = I R C2 \times R C2$ 

we assumed RC2 = 3.1k $\Omega$  and we know IRC2 = 3.33mA

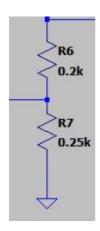
 $V RC2 = 3.1k\Omega \times 3.33 \text{ mA} \approx 10.5V$ 

V CC = V RE + 6V + 10.5V

We know that V RE =  $\{10-20\}\%$  x V CC and Vcc =  $\{6, 9, 12, 15, 18..\}$ 

Vcc = 18V so V RE = 1.5V

When we look that part of circuit clearly, we can see Voltage divider



 $VB = V E2 \times V RE22 / (V RE22 + V RE21)$ 

 $V B = 2V x (0.2k\Omega/0.25k\Omega) = 0.8V$ 

According to given hints:

V RE21 = V RE1 + V BEQ1 + V RB

After voltage divider we know that V RE21 = 1.4V

1.4V = 0.6V + 0.6V + V RE1

V RE1 = 0.2V

**Current Calculations:** 

$$I CQ2 = V OUT / (R C2 //R L) = 5V/1,5kΩ = 3,3 mA$$

We assuming that collector current equal to emitter current:

$$I CQ2 = I EQ1 = 3.3 mA$$

Since we have transistor with 200 beta value:

$$I BQ2 = I CQ2 / 200 = 0.016 mA$$

And also, we know that I CQ1 = I CQ2 / (2-10)

$$I CQ1 = I CQ2 / 10 = 3.33/10 = 0.3 \text{ mA}$$

$$I CQ1 = I EQ1 = 0.3 mA$$

So base current of First transistor (Beta value = 200) is:

$$I BQ1 = I CQ1 / 200 = 0.00165 mA$$

Resistor Calculations:

We assumed R C2 =  $3.1k\Omega$  (Because control the voltage on emitter branch)

At the second emitter branch we ignored the transistors 1's base current branch and we said R E2 =  $0.6k\Omega$ 

Now depends on proper voltage division divided values like:

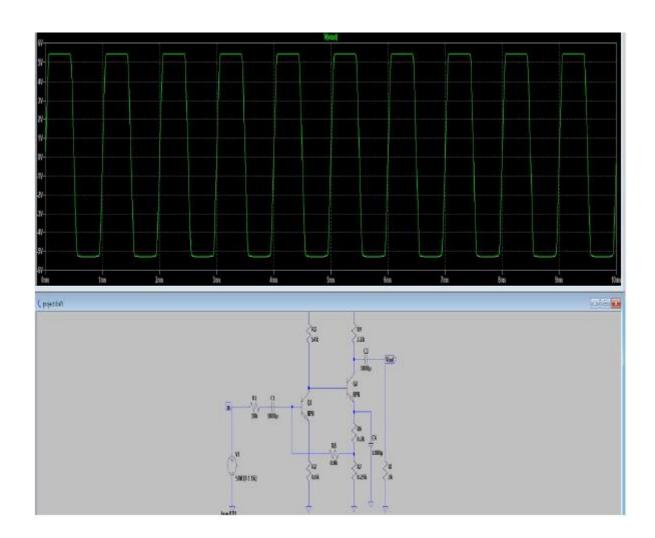
 $R E21 = 0.4k\Omega$ 

And

 $R E22 = 0.2k\Omega$ 

R E1 = V RE1 / I EQ1 = 
$$0.2V$$
 /  $0.3mA$  =  $0.6k\Omega$  R C1 = V CC / I CQ1 =  $18V$  /  $0.33mA$  =  $54k\Omega$ 

#### **Transient Analysis:**

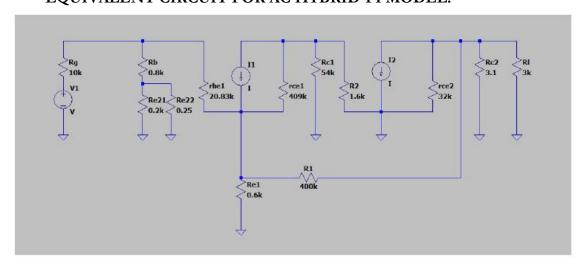


### Operational Point Analysis:

0	perating Point	-	
V(in):	О	voltage	
V(n005):	0.892101	voltage	
V(n004):	8.92101e-12	voltage	
V(n003):	2.41689	voltage	
V(n008):	0.153403	voltage	
V(vout):	2.10445e-11	voltage	
V(n002):	7.01484	voltage	
V(n006):	1.60993	voltage	
V(n001):	18	voltage	
V(n007):	0.894126	voltage	
Ic(Q2):	0.0035436	device current	
Ib (Q2):	3.5436e-05	device current	
Ie (Q2):	-0.00357903	device current	
Ic (Q1):	0.00025314	device current	
Ib (Q1):	2.5314e-06	device current	
Ie (Q1):	-0.000255672	device current	
I (C4):	1.60993e-15	device current	
I (C3):	-7.01484c-15	device current	
I(C1):	8.92101e-16	device current	
I(R8):	2.5314e-06	device current	
I(R7):	0.0035765	device current	
I (R6):	0.00357903	device current	
I(R1):	7.01484e-15	device current	
I(R4):	0.0035436	device current	
I(R3):	0.000288576	device current	
I (R2):	0.000255672	device current	
I(R1):	8.92101e-16	device current	
I(V2):	-0.00383217	device_current	
I(V1):	8.92101e-16	device current	

# **AC ANALYSIS**

### EQUIVALENT CIRCUIT FOR AC HYBRID-PI MODEL:



### **ADMITANCE MATRIX**

	1	2	3	4
1	$\frac{1}{RB + RE21} + BCQ1$	0	BCQ1	BEQ1
2	0	$\frac{1}{Rc2} + \frac{1}{Rf} + CCQ2 \text{ (Q2)}$	BCQ1	-1/Rf
3	CBQ1	BCQ2	$\frac{1}{Rc1} + BCQ1 + CCQ1$	CEQ1
4	EBQ1	-1/Rf	ECQ1	$CEQ1 + \frac{1}{RC} + 1/RF$

### Hybrid - pi parameters:

gm2 = ICQ2 / aT (aT value is equal to 26mV at room temperature)

$$gm2 = 3.3mA / 26mV = 0.12$$

$$rbe2 = \beta / gm$$

rbe2= 200 / 
$$0.12 = 1,6 \text{ k}\Omega$$

$$rce2 = (Va + VCEQ2) / ICQ2$$

Va = Early voltage which is 100V for our transistor

$$rce2 = (100 + 6) / 3.3 \text{mA} = 32 \text{k}\Omega$$

$$gm1 = 0.3mA / 26mV = 0.013$$

rbe1= 200 / 
$$0.012 = 16,66 \text{ k}\Omega$$

$$rce1 = (100 + 2.5) / 0.3 \text{mA} = 310 \text{k}\Omega$$

#### Calculations for Ku O

$$Ku \mathbf{O} = Ku \mathbf{O2} * Ku \mathbf{O1}$$

$$Ku O1 = -gm * R O * (Rbe / (Rbe + (201)*R1))$$

$$R \mathbf{O} = \text{Rce}(1) / / \text{Rc} 1 / / \text{Rbe}(2)$$

$$R \mathbf{O} = 310k\Omega//54k\Omega//310k\Omega$$

$$R1 = Re1 // Rf$$

$$R1 = 0.6k\Omega // 400k\Omega$$

$$R1 = 0.6k\Omega$$

$$Ku O2 = -gm * R O2$$

$$R O2 = Rce(2) // Rc2 // R2 // R1$$

$$R2 = Re1 + Rf$$

$$R2 = 400.6 \text{ k}\Omega$$

$$R \mathbf{O2} = 32k\Omega // 3.1k\Omega // 400.6 k\Omega // 3k\Omega$$

$$Ku$$
 **O2** = -0.013 \* 1549 $k$ Ω

### Small Signal Parameters:

$$Ku \mathbf{O} = Ku \mathbf{O2} * Ku \mathbf{O1}$$

$$Ku \mathbf{O} = -20.137 * -26.00$$

We have to apply Miller's theorem and consider Rm resistors. We know that we are eliminating Rm resistor at output of circuit so we only have Rm resistor Series to rbe1 and parallel to Rb, Re21 and Re22 with value of  $(1+\beta)$  RE1. After Miller's theorem our circuit will looking like that:

According that information we can perform calculations:

$$Rin o = Rbe(1) + (201) * R1$$

Rin o = 
$$140.6 \text{ k}\Omega$$

Rout 
$$o = rce(2) // Rc2 // R2$$

Rout 
$$o = 2724 \Omega$$

$$Rinf = Rin o * F$$

$$F = 1 + \text{Re}1/(\text{Re}1 + \text{Rf}) * \text{Ku o}$$

$$F = 216k\Omega$$

$$Rinf = 216k\Omega * 120k\Omega$$

$$Rinf = 45 M\Omega$$

$$Rin = (Rb+(Re21//Re22)) // Rinf$$

$$Rin = 0.9 \text{ k}\Omega$$

$$\varphi$$
u = Rin o //(Rb+(Re21//Re22)) / Rin o

$$//(Rb+(Re21//Re22)) + Rg$$

$$\varphi u = 0.08 \text{ k}\Omega$$

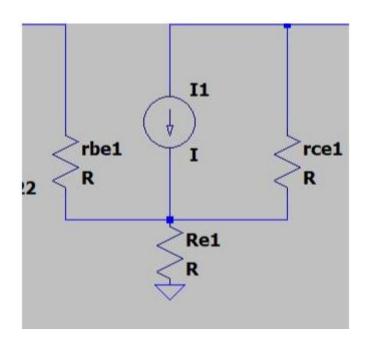
Kuef o = 
$$\varphi$$
u \* Ku $\mathbf{O}$  \* ( Rout o + Rl)/Rl

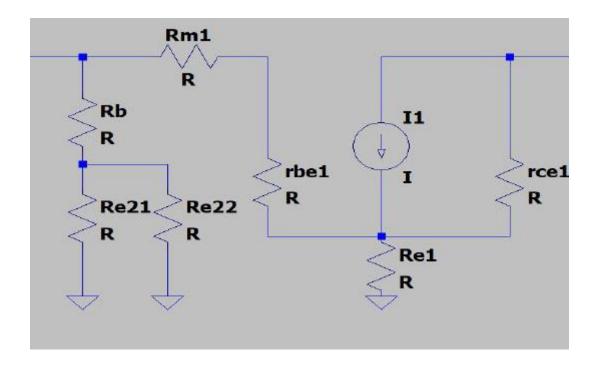
Kuef o = 
$$0.08 * 523.56 * 1.9$$

Kuef o = 
$$89.68 [V/V]$$

$$\underline{\text{Kuef o} = 39.08 \text{ dB}}$$

# resistor at that point:





Special words to our professor.

Dear Dr. Rafał Zdunek, we would like to thank you for your time and sincere effort throughout this semester that has been particularly challenging for all of us. We would like hereby to express our gratitude for your engagement and support.

Cordially,

Nick Ntsouini-Bitoumi and Mert Çetin.